
2SK3211(L), 2SK3211(S)

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

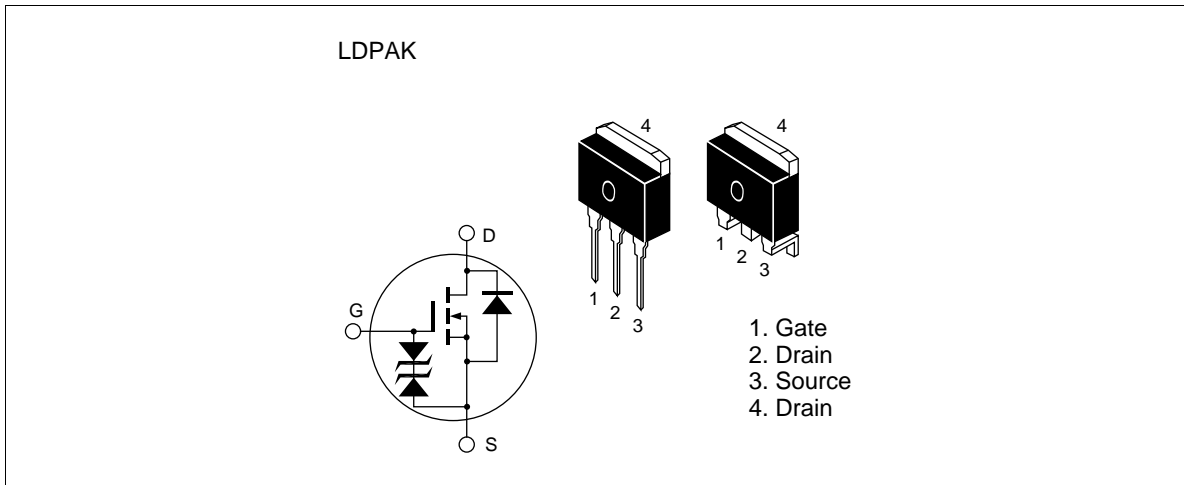
ADE-208-761A (Z)
2nd. Edition
February 1999

Features

- Low on-resistance
 $R_{DS} = 60 \text{ m}\Omega$ typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

2SK3211

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	200	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	25	A
Drain peak current	$I_{D(pulse)}^{*1}$	100	A
Body-drain diode reverse drain current	I_{DR}	25	A
Avalanche current	I_{AP}^{*3}	25	A
Avalanche energy	E_{AR}^{*3}	41	mJ
Channel dissipation	P_{ch}^{*2}	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

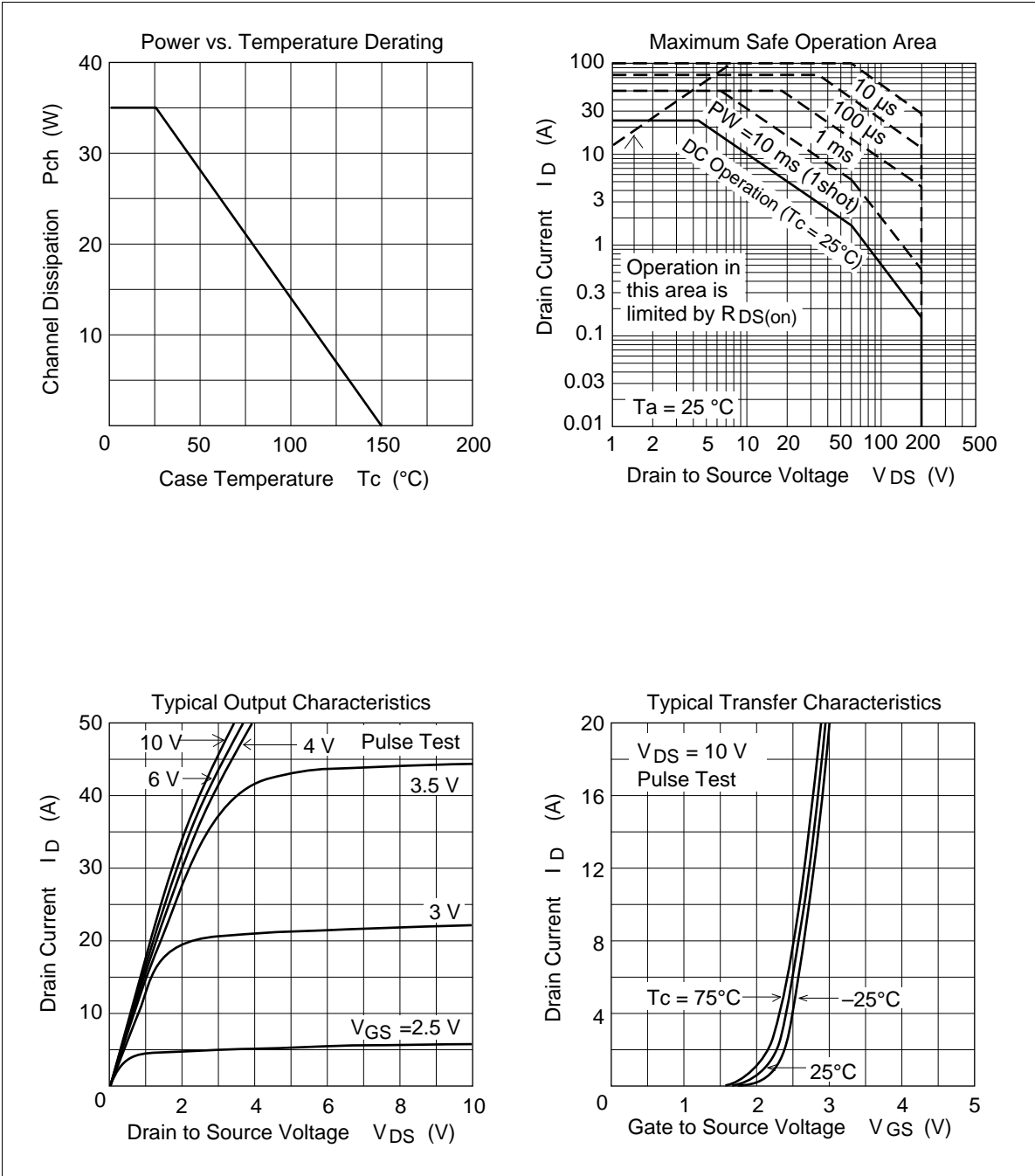
Note: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$
3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$

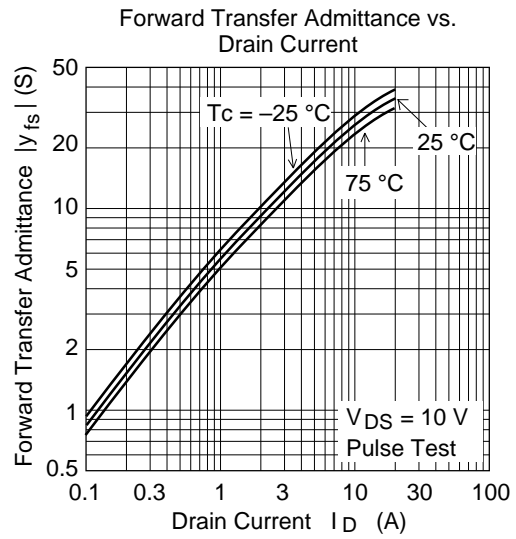
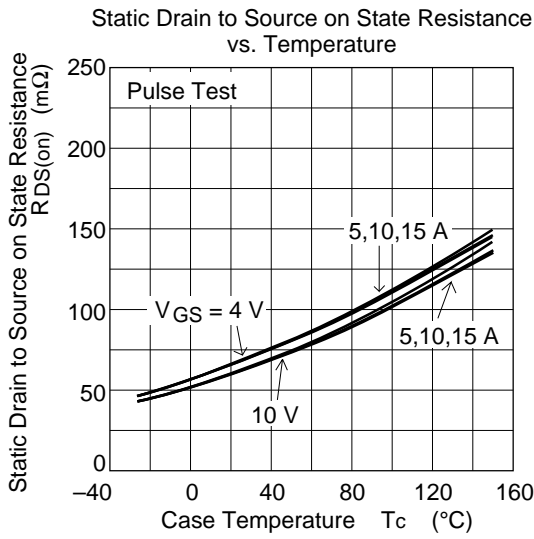
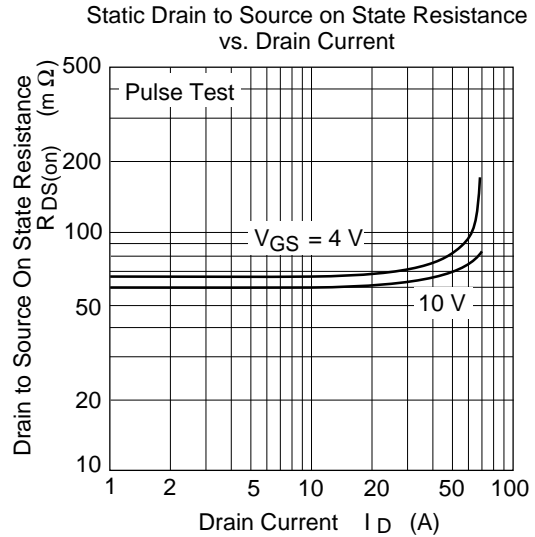
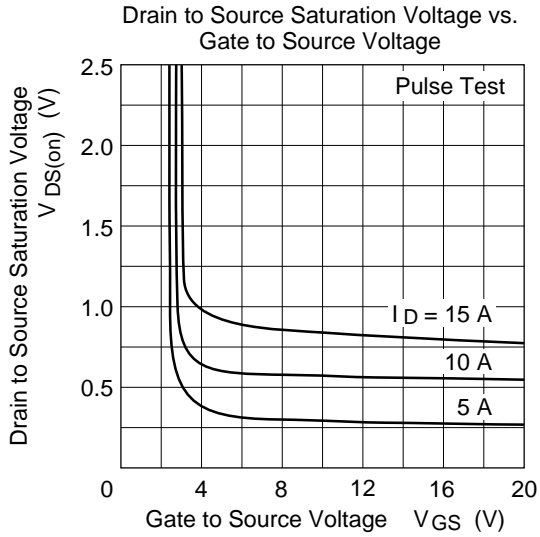
Electrical Characteristics (Ta = 25°C)

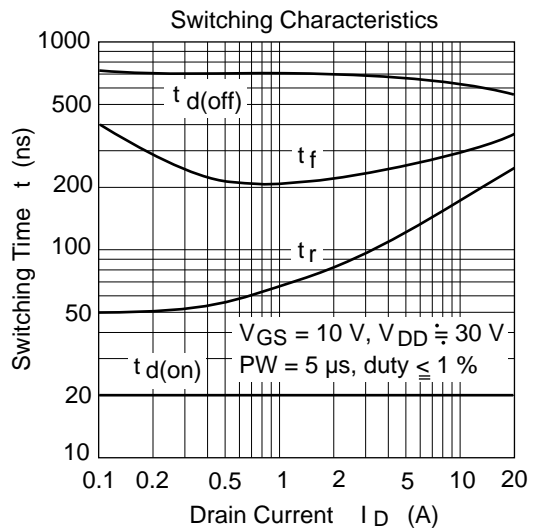
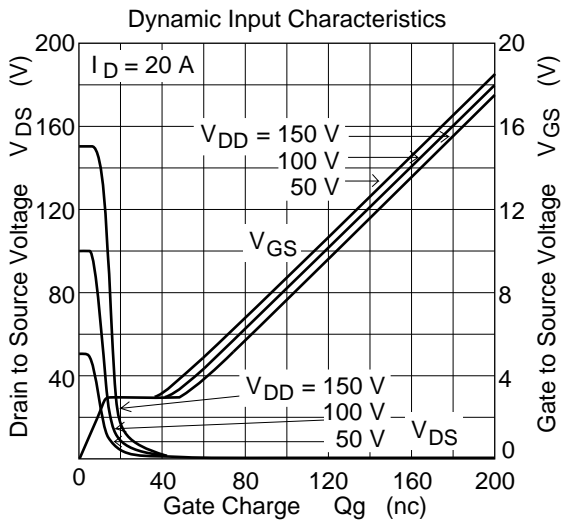
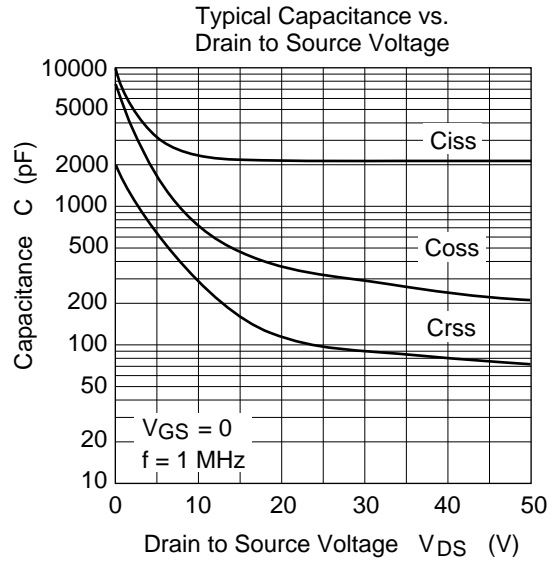
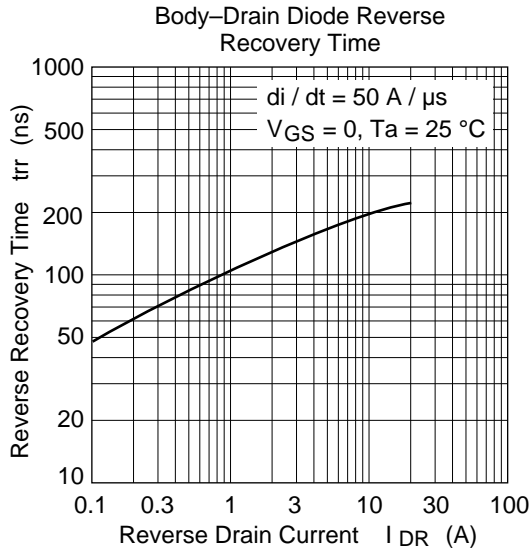
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	60	75	m Ω	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{*4}$
	$R_{DS(on)}$	—	65	85	m Ω	$I_D = 15 \text{ A}, V_{GS} = 4 \text{ V}^{*4}$
Forward transfer admittance	$ y_{fs} $	18	30	—	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{*4}$
Input capacitance	Ciss	—	2420	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	Coss	—	790	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	340	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}$
Rise time	t_r	—	230	—	ns	$R_L = 2 \text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	—	590	—	ns	
Fall time	t_f	—	330	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_F = 25 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	230	—	ns	$I_F = 25 \text{ A}, V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

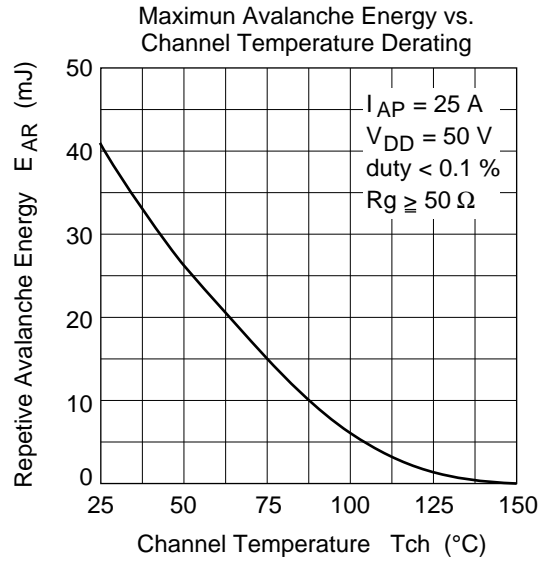
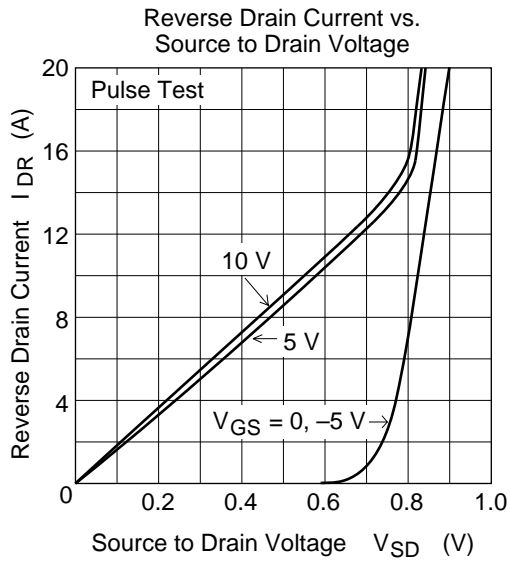
Note: 4. Pulse test

Main Characteristics

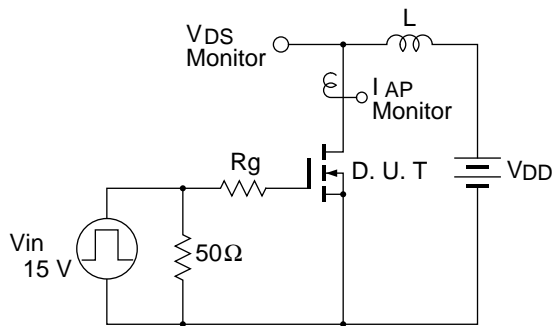




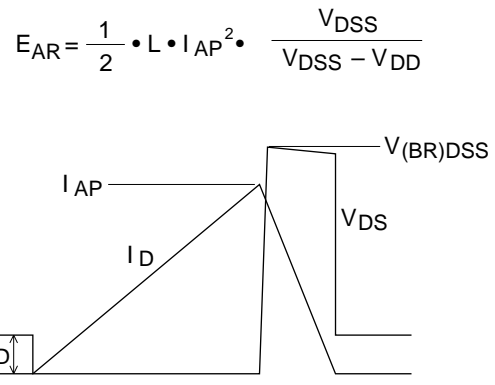


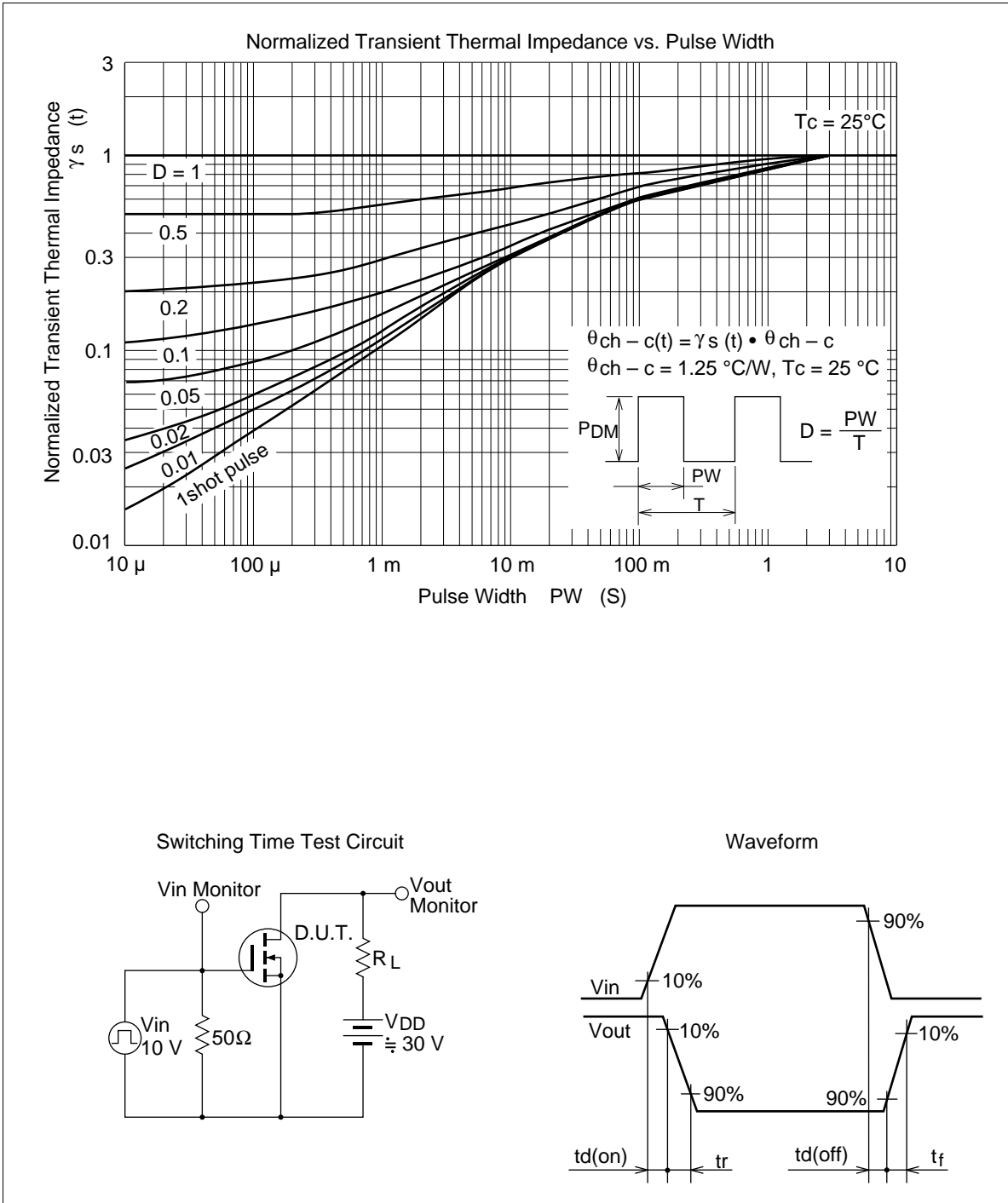


Avalanche Test Circuit



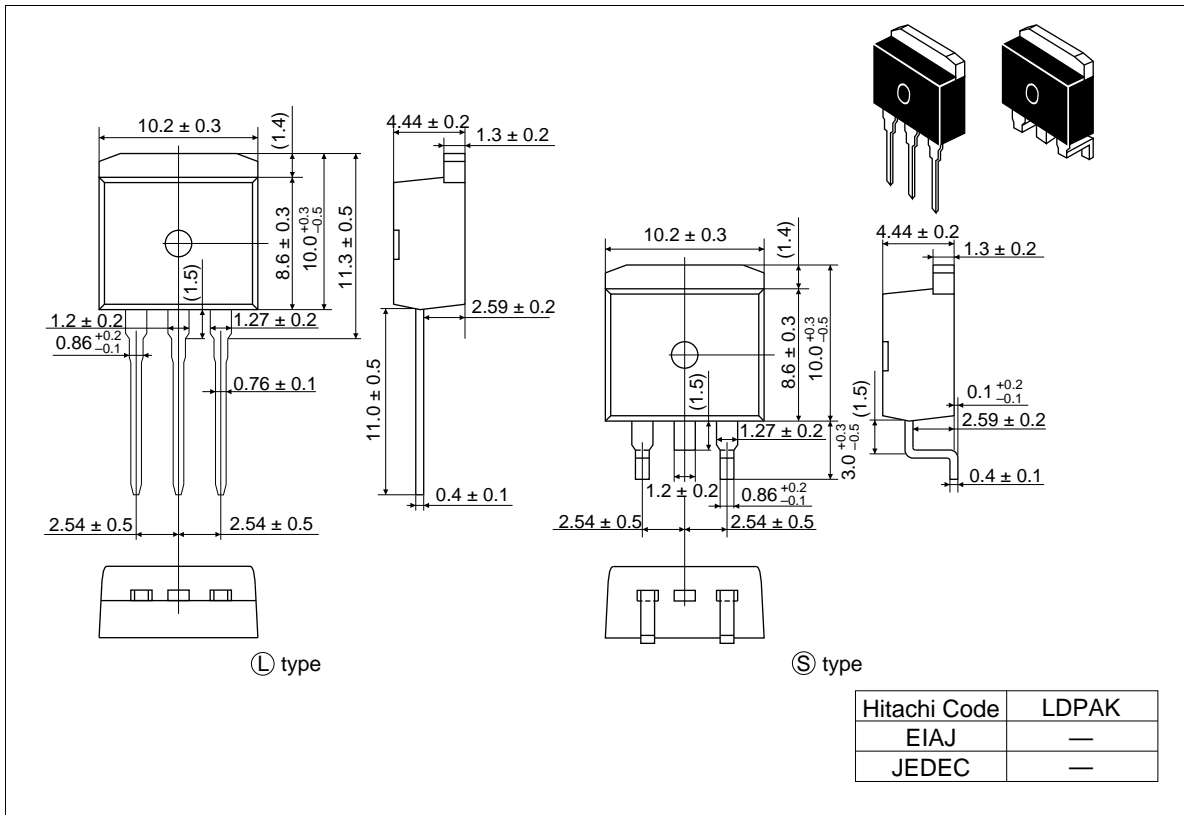
Avalanche Waveform





Package Dimensions

Unit: mm



2SK3211

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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Domacher StraÙe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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